Programmable Precision References

The NCP431/NCP432 integrated circuits are three-terminal programmable shunt regulator diodes. These monolithic IC voltage references operate as a low temperature coefficient zener which is programmable from Vref to 36 V using two external resistors. These devices exhibit a wide operating current range of 40 μ A to 100 mA with a typical dynamic impedance of 0.22 Ω . The characteristics of these references make them excellent replacements for zener diodes in many applications such as digital voltmeters, power supplies, and op amp circuitry. The 2.5 V reference makes it convenient to obtain a stable reference from 5.0 V logic supplies, and since the NCP431/NCP432 operates as a shunt regulator, it can be used as either a positive or negative voltage reference. Low minimum operating current makes this device an ideal choice for secondary regulators in SMPS adapters with extremely low no-load consumption.

Features

- Programmable Output Voltage to 36 V
- Low Minimum Operating Current: 40 μA, Typ @ 25°C
- Voltage Reference Tolerance: ±0.5%, Typ @ 25°C (NCP431B/NCP432B)
- Low Dynamic Output Impedance, 0.22Ω Typical
- Sink Current Capability of 40 µA to 100 mA
- Equivalent Full-Range Temperature Coefficient of 50 ppm/°C Typical
- Temperature Compensated for Operation over Full Rated Operating Temperature Range
- SC Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These are Pb–Free Devices

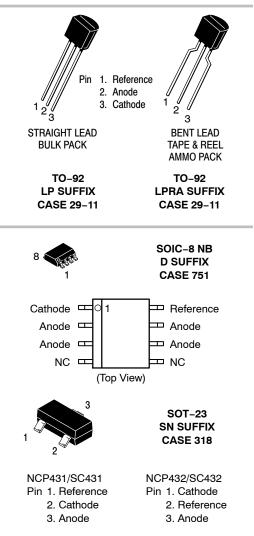
Typical Applications

- Voltage Adapters
- Switching Power Supply
- Precision Voltage Reference
- Charger
- Instrumentation



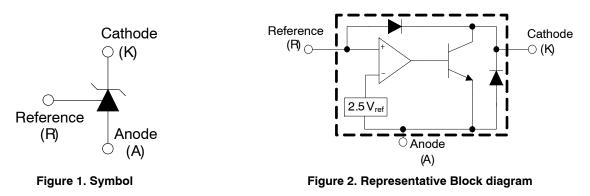
ON Semiconductor®





ORDERING AND MARKING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 14 of this data sheet.



This device contains 20 active transistors

MAXIMUM RATINGS (Full operating ambient temperature range applies, unless otherwise noted)
--

Symbol	Rating	Value	Unit
V _{KA}	Cathode to Anode Voltage	37	V
Ι _Κ	Cathode Current Range, Continuous	–100 to +150	mA
I _{ref}	Reference Input Current Range, Continuous	–5 to +10	mA
TJ	Operating Junction Temperature	150	°C
T _A	Operating Ambient Temperature Range	-40 to +125	°C
T _{stg}	Storage Temperature Range	-65 to +150	°C
PD	Total Power Dissipation @ T _A = 25°C Derate above 25°C Ambient Temperature D, LP Suffix Plastic Package SN1 Suffix Plastic Package	0.70 0.52	W
P _D	Total Power Dissipation @ T _C = 25°C Derate above 25°C Case Temperature D, LP Suffix Plastic Package	1.5	W
HBM CDM	ESD Rating (Note 1) Human Body Model per JEDEC JESD22-A114F Charged Device Model per JEDEC JESD22-C101E	>2000 >1000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. This device contains latch-up protection and exceeds ±100 mA per JEDEC standard JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Condition	Min	Max	Unit
V _{KA}	Cathode to Anode Voltage	V _{ref}	36	V
۱ _K	Cathode Current	0.04	100	mA

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

THERMAL CHARACTERISTICS

Symbol	Characteristic	LP Suffix Package (50 mm ² x 35 μm Cu)	D Suffix Package (50 mm ² x 35 μm Cu)	SN Suffix Package (10 mm ² x 35 μm Cu)	Unit
$R_{\Theta JA}$	Thermal Resistance, Junction-to-Ambient	176	210	255	°C/W
R _{ØJL}	Thermal Resistance, Junction-to-Lead (Lead 3)	75	68	80	°C/W

		NCP431AC			NCP431AI			N S			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
V _{ref}	Reference Input Voltage $V_{KA} = V_{ref}, I_K = 1 \text{ mA}$ $T_A = 25^{\circ}C$ $T_A = T_{low}$ to T_{high} (Figure 3, Note 2)		2.500 2.500	2.525 2.525	2.475 2.465		2.525 2.525		2.500 2.500	2.525 2.525	V
ΔV_{refT}	Reference Input Voltage Deviation Over Temperature Range (Figure 3, Notes 3, 4) V_{KA} = V_{ref} , I_K = 1 mA	-	-	-	_	5.0	10	_	10	15	mV
$\frac{\Delta V_{\text{ref}}}{\Delta V_{\text{KA}}}$	Ratio of Change in Reference Input Voltage to Change in Cathode to Anode Voltage $I_K = 1 \text{ mA}$ (Figure 4), $\Delta V_{KA} = 10 \text{ V to } V_{ref}$ $\Delta V_{KA} = 36 \text{ V to } 10 \text{ V}$		-1.85 -0.80	-3.1 -1.8		-1.85 -0.80	-3.1 -1.8		-1.85 -0.80	-3.1 -1.8	mV/ V
I _{ref}	Reference Input Current (Figure 4) $I_{K} = 1 \text{ mA}, \text{ R1} = 220 \text{ k}, \text{ R2} = \infty$ $T_{A} = -40^{\circ}\text{C} \text{ to } +125^{\circ}\text{C}$	-	81	190	-	81	190	-	81	190	nA
ΔI_{refT}	Reference Input Current Deviation Over Temperature Range (Figure 4, Note 3) $I_{K} = 1 \text{ mA}, R1 = 10 \text{ k}, R2 = \infty$	-	22	55	-	22	55	-	22	55	nA
I _{min}	Minimum Cathode Current For Regulation $V_{KA} = V_{ref}$ (Figure 3)	-	40	60	_	40	60	-	40	60	μA
I _{off}	Off-State Cathode Current (Figure 5) V _{KA} = 36 V, V _{ref} = 0 V	-	180	1000	_	180	1000	-	180	1000	nA
Z _{KA}	Dynamic Impedance (Figure 3, Note 5) $V_{KA} = V_{ref}, \Delta I_K = 1.0 \text{ mA to } 100 \text{ mA}$ f $\leq 1.0 \text{ kHz}$	-	0.22	0.5	_	0.22	0.5	-	0.22	0.5	Ω

ELECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise noted.)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. T_{low} = -40°C for NCP431AI, NCP431AV, SC431AV

= 0°C for NCP431AC

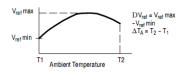
T_{high} = 70°C for NCP431AC

= 85°C for NCP431AI

= 125°C for NCP431AV, SC431AV

3. Guaranteed by design

The deviation parameter ΔV_{refT} is defined as the difference between the maximum and minimum values obtained over the full operating 4. ambient temperature range that applies.



The average temperature coefficient of the reference input voltage, Vref is defined as:

$$v_{ref} \frac{ppm}{^{\circ}C} = \frac{\left(\frac{\Delta V_{ref}}{V_{ref} ^{(@25^{\circ}C)}}\right) \times 10^{6}}{\Delta T_{A}} = \frac{\Delta V_{ref} \times 10^{6}}{\Delta T_{A} (V_{ref} ^{(@25^{\circ}C)})}$$

aVref can be positive or negative depending on whether Vref Min or Vref Max occurs at the lower ambient temperature.

Example: ΔV_{refT} = 17 mV and slope is positive $V_{ref} = 2.5 \text{ V}, \Delta T_A = 165^{\circ}\text{C} \text{ (from } -40^{\circ}\text{C to } +125^{\circ}\text{C} \text{)}$

$$\alpha V_{\text{ref}} = \frac{0.017 \cdot 10^6}{165 \cdot 2.5} = 41.2 \text{ ppm/}^\circ \text{C}$$

- The dynamic impedance Z_{KA} is defined as: (|Z_{KA}| = (ΔV_{KA}/ΔI_K). When the device is programmed with two external resistors, R1 and R2, the total dynamic impedance of the circuit is defined as: |Z_{KA}| ≈ |Z_{KA}| (1 + (R1/R2)).
 SC431AVSNT1G T_{low} = -40°C, T_{high} = 125°C. Guaranteed by design. SC Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

		NCP431BC NCP432BC			NCP431BI NCP432BI			NCP/SC431BV NCP/SC432BV			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
V _{ref}	Reference Input Voltage $V_{KA} = V_{ref}, I_K = 1 \text{ mA}$ $T_A = 25^{\circ}C$ $T_A = T_{low}$ to T _{high} (Figure 3, Note 7)				2.4875 2.4775						V
ΔV_{refT}	Reference Input Voltage Deviation Over Temperature Range (Figure 3, Notes 8, 9) V_{KA} = V_{ref} , I_{K} = 1 mA	-	-	-	-	5.0	10 1-	-	10	15 15	mV
$\frac{\Delta V_{\text{ref}}}{\Delta V_{\text{KA}}}$	Ratio of Change in Reference Input Voltage to Change in Cathode to Anode Voltage $I_K = 1 \text{ mA}$ (Figure 4), $\Delta V_{KA} = 10 \text{ V to } V_{ref}$ $\Delta V_{KA} = 36 \text{ V to } 10 \text{ V}$		-1.85 -0.80	-3.1 -1.8		-1.85 -0.80	-3.1 -1.8		-1.85 -0.80	-3.1 -1.8	mV/ V
I _{ref}	Reference Input Current (Figure 4) $I_K = 1 \text{ mA}, \text{ R1} = 220 \text{ k}, \text{ R2} = \infty$ $T_A = -40^{\circ}\text{C} \text{ to } +125^{\circ}\text{C}$	-	81	190	-	81	190	-	81	190	nA
ΔI_{refT}	Reference Input Current Deviation Over Temperature Range (Figure 4, Note 8) $I_K = 1 \text{ mA}, R1 = 10 \text{ k}, R2 = \infty$	-	22	55	-	22	55	-	22	55	nA
I _{min}	Minimum Cathode Current For Regulation $V_{KA} = V_{ref}$ (Figure 3)	-	40	60	-	40	60	_	40	60	μA
I _{off}	Off-State Cathode Current (Figure 5) V _{KA} = 36 V, V _{ref} = 0 V	-	180	1000	-	180	1000	_	180	1000	nA
Z _{KA}	Dynamic Impedance (Figure 3, Note 10) $V_{KA} = V_{ref}, \Delta I_K = 1.0 \text{ mA to } 100 \text{ mA}$ f $\leq 1.0 \text{ kHz}$	-	0.22	0.5	-	0.22	0.5	-	0.22	0.5	Ω

ELECTRICAL CHARACTERISTICS (T. 25°C unloss otherwise noted)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

7. T_{low} = -40°C for NCP431BI, NCP431BV, NCP432BI, NCP432BV, SC431B, SC432B

= 0°C for NCP431BC, NCP432BC

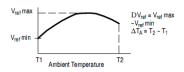
T_{high} = 70°C for NCP431BC, NCP432BC

= 85°C for NCP431BI, NCP432BI

= 125°C for NCP431BV, NCP432BV, SC431BV, SC432BV

8. Guaranteed by design

The deviation parameter ΔV_{refT} is defined as the difference between the maximum and minimum values obtained over the full operating 9. ambient temperature range that applies.



The average temperature coefficient of the reference input voltage, Vref is defined as:

$$v_{ref} \frac{ppm}{^{\circ}C} = \frac{\left(\frac{\Delta V_{ref}}{V_{ref} @25^{\circ}C}\right) \times 10^{6}}{\Delta T_{A}} = \frac{\Delta V_{ref} \times 10^{6}}{\Delta T_{A} \left(V_{ref} @25^{\circ}C\right)}$$

aVref can be positive or negative depending on whether Vref Min or Vref Max occurs at the lower ambient temperature.

Example: ΔV_{refT} = 17 mV and slope is positive $V_{ref} = 2.5 \text{ V}, \Delta T_A = 165^{\circ}\text{C} \text{ (from } -40^{\circ}\text{C to } +125^{\circ}\text{C} \text{)}$

$$\alpha V_{\text{ref}} = \frac{0.017 \cdot 10^6}{165 \cdot 2.5} = 41.2 \text{ ppm/}^\circ \text{C}$$

- 10. The dynamic impedance Z_{KA} is defined as: ($|Z_{KA}| = (\Delta V_{KA} / \Delta I_K)$). When the device is programmed with two external resistors, R1 and R2,
- the total dynamic impedance Z_KA is defined us: (|Z_KA| = (Z_KA/Z_K), when the device is programmed with two external resistors, fit and fiz, the total dynamic impedance of the circuit is defined as: |Z_KA| ≈ |Z_KA| (1 + (R1/R2))
 SC431BVSNT1G, SC432BVSNT1G T_{low} = -40°C, T_{high} = 125°C. Guaranteed by design. SC Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

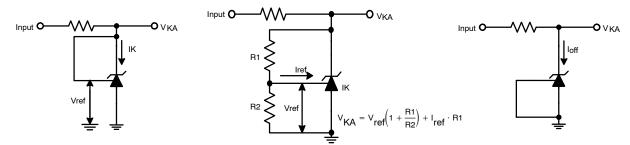
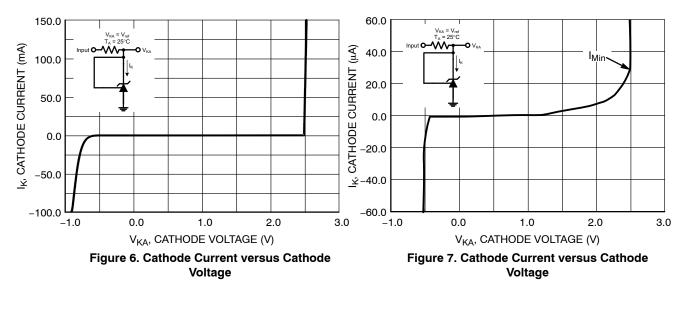
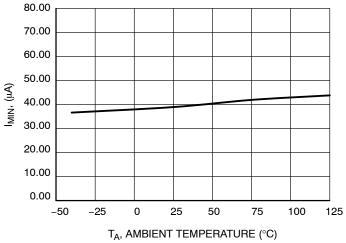


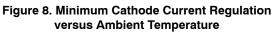
Figure 3. Test Circuit for $V_{KA} = V_{ref}$

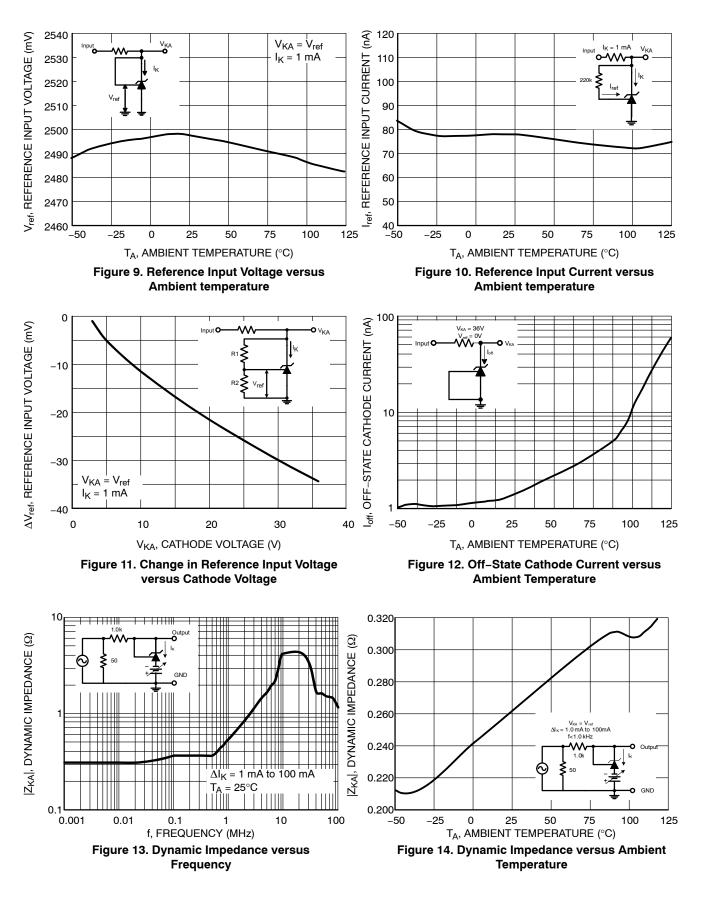
Figure 4. Test Circuit for V_{KA} > V_{ref} Figure

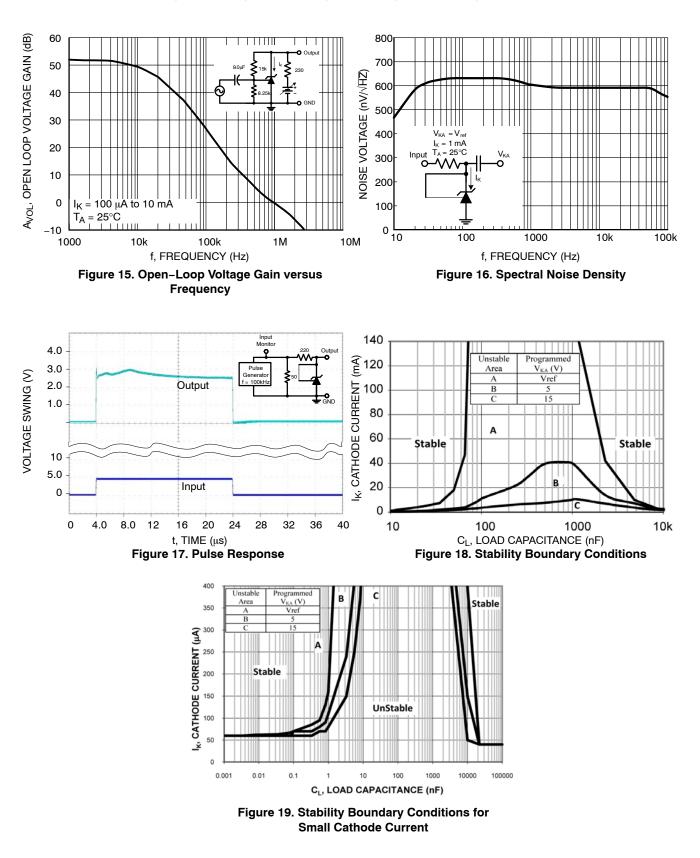
Figure 5. Test Circuit for Ioff











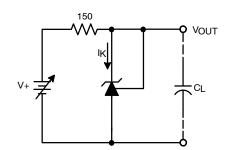


Figure 20. Test Circuit For Curve A of Stability Boundary Conditions

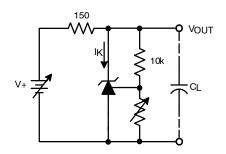


Figure 21. Test Circuit For Curve B And C of Stability Boundary Conditions

TYPICAL APPLICATIONS

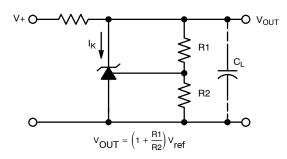
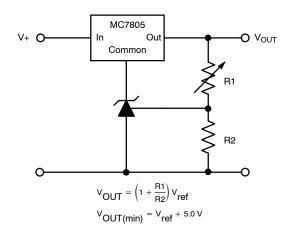


Figure 22. Shunt Regulator





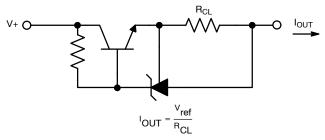


Figure 26. Constant Current Source

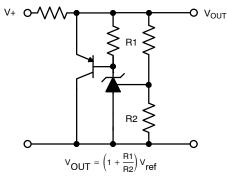


Figure 23. High Current Shunt Regulator

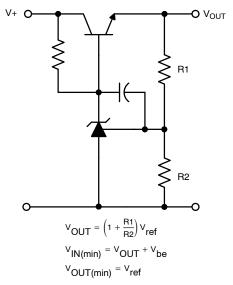


Figure 25. Series Pass Regulator

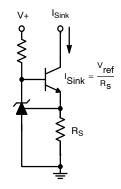


Figure 27. Constant Current Sink

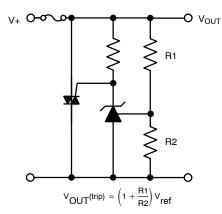


Figure 28. Triac Crowbar

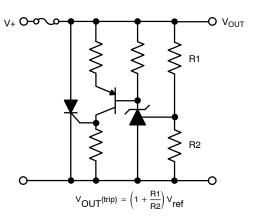
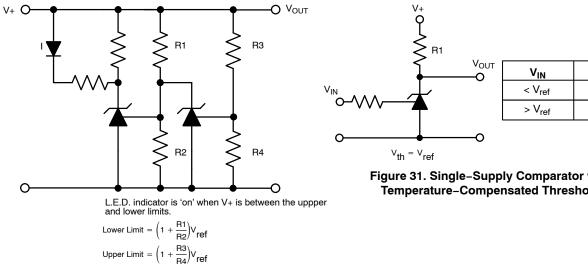


Figure 29. SRC Crowbar

V_{OUT}

V+

≈2.0 V







Temperature-Compensated Threshold

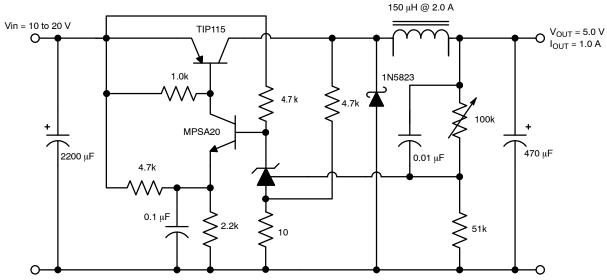


Figure 32. Step-Down Switching Converter

APPLICATIONS INFORMATION

The NCP431/NCP432 is a programmable precision reference which is used in a variety of ways. It serves as a reference voltage in circuits where a non-standard reference voltage is needed. Other uses include feedback control for driving an optocoupler in power supplies, voltage monitor, constant current source, constant current sink and series pass regulator. In each of these applications, it is critical to maintain stability of the device at various operating currents and load capacitances. In some cases the circuit designer can estimate the stabilization capacitance from the stability boundary conditions curve provided in Figure 18. However, these typical curves only provide stability information at specific cathode voltages and at a specific load condition. Additional information is needed to determine the capacitance needed to optimize phase margin or allow for process variation.

A simplified model of the NCP431/NCP432 is shown in Figure 33. When tested for stability boundaries, the load resistance is 150 Ω . The model reference input consists of an input transistor and a dc emitter resistance connected to the device anode. A dependent current source, Gm, develops a current whose amplitude is determined by the difference between the 1.78 V internal reference voltage source and the input transistor emitter voltage. A portion of Gm flows through compensation capacitance, CP2. The voltage across CP2 drives the output dependent current source, Go, which is connected across the device cathode and anode.

Model component values are:

Vref = 1.78 V

 $Gm = 0.3 + 2.7 \exp(-IC/26 mA)$

where IC is the device cathode current and Gm is in mhos Go = 1.25 (Vcp2) µmhos.

Resistor and capacitor typical values are shown on the model. Process tolerances are $\pm 20\%$ for resistors, $\pm 10\%$ for capacitors, and $\pm 40\%$ for transconductances.

An examination of the device model reveals the location of circuit poles and zeroes:

P1 =
$$\frac{1}{2\pi R_{GM}C_{P1}} = \frac{1}{2\pi \cdot 1.0M \cdot 20 \text{ pF}} = 7.96 \text{ kHz}$$

P2 =
$$\frac{1}{2\pi R_{P2}C_{P2}} = \frac{1}{2\pi \cdot 10M \cdot 0.265 \text{ pF}} = 60 \text{ kHz}$$

Z1 =
$$\frac{1}{2\pi R_{Z1}C_{P1}} = \frac{1}{2\pi \cdot 15.9k \cdot 20 \text{ pF}} = 500 \text{ kHz}$$

In addition, there is an external circuit pole defined by the load:

$$\mathsf{P}_{\mathsf{L}} = \frac{1}{2\pi\mathsf{R}_{\mathsf{L}}\mathsf{C}_{\mathsf{L}}}$$

Also, the transfer dc voltage gain of the NCP431 is:

$$G = G_M R_{GM} Go R_L$$

Example 1:

 $I_C=10$ mA, $R_L=230 \Omega$, $C_L=0$. Define the transfer gain. The DC gain is:

$$G = G_M R_{GM} GoR_L = (2.138)(1.0M)(1.25\mu)(230)$$

= 615 = 56 dB

Loop gain =
$$G \frac{8.25k}{8.25k + 15k} = 218 = 47 \text{ dB}$$

The resulting transfer function Bode plot is shown in Figure 34. The asymptotic plot may be expressed as the following equation:

$$Av = 615 \frac{\left(1 + \frac{jf}{500 \text{ kHz}}\right)}{\left(1 + \frac{jf}{8.0 \text{ kHz}}\right)\left(1 + \frac{jf}{60 \text{ kHz}}\right)}$$

The Bode plot shows a unity gain crossover frequency of approximately 600 kHz. The phase margin, calculated from the equation, would be 55.9° . This model matches the Open–Loop Bode Plot of Figure 15. The total loop would have a unity gain frequency of about 300 kHz with a phase margin of about 44°.

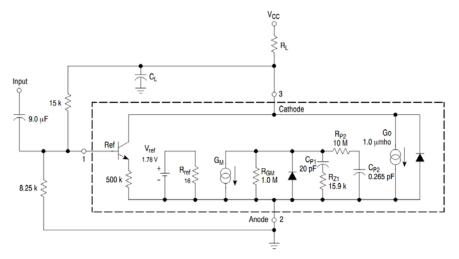


Figure 33. Simplified NCP431/NCP432 Device Model

NCP431/NCP432 OPEN-LOOP VOLTAGE GAIN VERSUS FREQUENCY

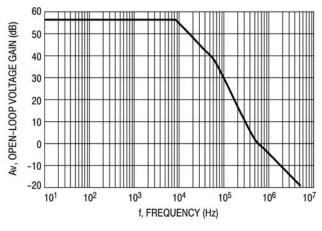


Figure 34. Example 1 Circuit Open Loop Gain Plot

Example 2.

 $I_C = 7.5$ mA, $R_L = 2.2$ k Ω , $C_L = 0.01 \mu$ F. Cathode tied to reference input pin. An examination of the data sheet stability boundary curve (Figure 18) shows that this value of load capacitance and cathode current is on the boundary.

Define the transfer gain.

The DC gain is:

 $G = G_M R_{GM} GoR_L = (2.138)(1.0M)(1.25\mu)(230)$ = 6389 = 76 dB

The resulting open loop Bode plot is shown in Figure 35. The asymptotic plot may be expressed as the following equation:

$$Av = 615 \frac{\left(1 + \frac{jf}{500 \text{ kHz}}\right)}{\left(1 + \frac{jf}{8.0 \text{ kHz}}\right)\left(1 + \frac{jf}{60 \text{ kHz}}\right)\left(1 + \frac{jf}{7.2 \text{ kHz}}\right)}$$

Note that the transfer function now has an extra pole formed by the load capacitance and load resistance.

Note that the crossover frequency in this case is about 250 kHz, having a phase margin of about -46° . Therefore, instability of this circuit is likely.

NCP431/NCP432 OPEN-LOOP BODE PLOT WITH LOAD CAP

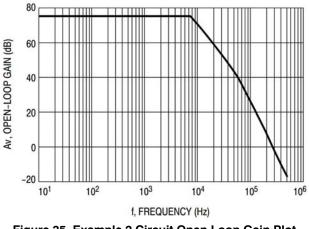


Figure 35. Example 2 Circuit Open Loop Gain Plot

With three poles, this system is unstable. The only hope for stabilizing this circuit is to add a zero. However, that can only be done by adding a series resistance to the output capacitance, which will reduce its effectiveness as a noise filter. Therefore, practically, in reference voltage applications, the best solution appears to be to use a smaller value of capacitance in low noise applications or a very large value to provide noise filtering and a dominant pole rolloff of the system.

The NCP431/NCP432 is often used as a regulator in secondary side of a switch mode power supply (SMPS).

The benefit of this reference is high and stable gain under low bias currents. Figure 36 shows dependence of the gain (dynamic impedance) on the bias current. Value of minimum cathode current that is needed to assure stable gain is 80 μ A maximum.

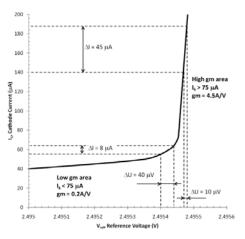


Figure 36. Knee of Reference

Regulator with TL431 or other references in secondary side of a SMPS needs bias resistor to increase cathode current to reach high and stable gain (refer to Figure 37). This bias resistor does not have to be used in regulator with NCP431/NCP432 thanks to its low minimum cathode current.

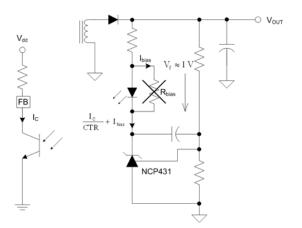
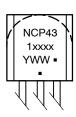


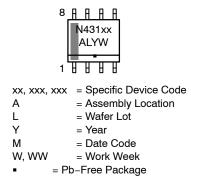
Figure 37. SMPS Secondary Side and Feedback Connection on Primary Side

The NCP431/NCP432 operates with very low leakage and reference input current. Sum of these currents is lower than 100 nA. Regulator with the NCP431/NCP432 minimizes parasitic power consumption.

The best way to achieve extremely low no-load consumption in SMPS applications is to use NCP431/NCP432 as regulator on the secondary side. The consumption is reduced by minimum parasitic consumption and very low bias current of NCP431/NCP432.

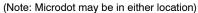


MARKING DIAGRAMS



xxx M=

•



ORDERING INFORMATION

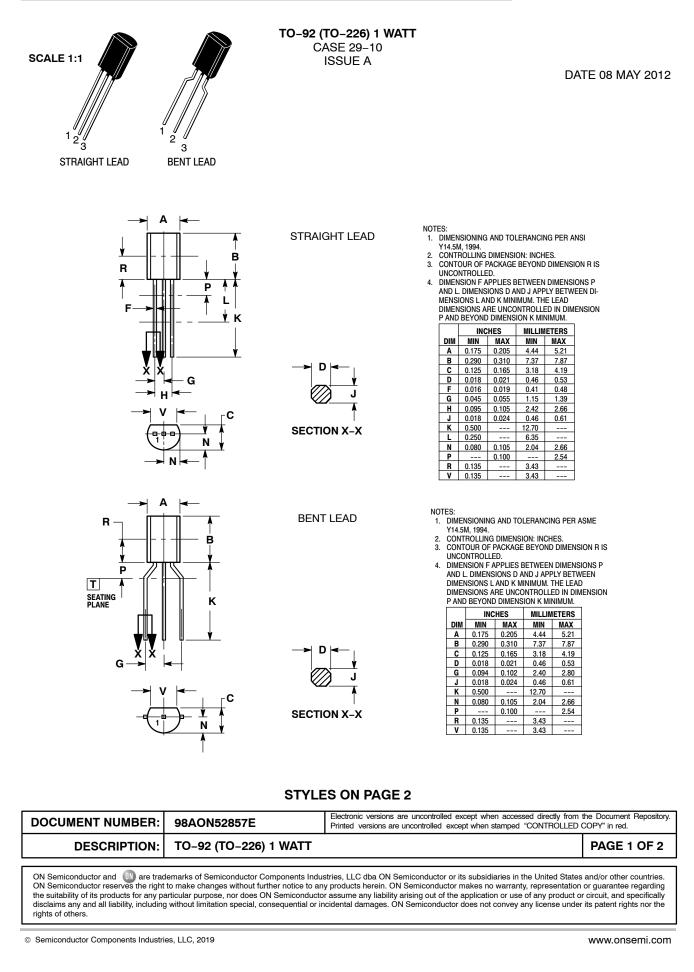
Device	Marking	Tolerance	Operating Temperature Range	Package	Shipping [†]
NCP431ACDR2G	AC	1%		SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCP431ACSNT1G	VRF	1%		SOT-23-3 (Pb-Free)	3000 / Tape & Reel
NCP431BCSNT1G	VRJ	0.5%	0°C to 70°C	SOT-23-3 (Pb-Free)	3000 / Tape & Reel
NCP432BCSNT1G	VRM	0.5%		SOT-23-3 (Pb-Free)	3000 / Tape & Reel
NCP431ACLPRAG	ACLP	1%		TO-92 (TO-226) (Pb-Free)	2000 / Tape & Reel
NCP431AIDR2G	AI	1%		SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCP431AISNT1G	VRG	1%		SOT-23-3 (Pb-Free)	3000 / Tape & Reel
NCP431BISNT1G	VRK	0.5%	–40°C to 85°C	SOT-23-3 (Pb-Free)	3000 / Tape & Reel
NCP432BISNT1G	VRN	0.5%		SOT-23-3 (Pb-Free)	3000 / Tape & Reel
NCP431AILPRAG	AILP	1%		TO-92 (TO-226) (Pb-Free)	2000 / Tape & Reel
NCP431AVDR2G	AV	1%		SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCP431AVSNT1G / SC431AVSNT1G*	VRH	1%		SOT-23-3 (Pb-Free)	3000 / Tape & Reel
NCP431AVLPRAG	AVLP	1%		TO-92 (TO-226) (Pb-Free)	2000 / Tape & Reel
NCP431AVLPG	AVLP	1%	–40°C to 125°C	TO-92 (TO-226) (Pb-Free)	2000 Units / Bag
NCP431BVSNT1G / SC431BVSNT1G*	VRL	0.5%		SOT-23-3 (Pb-Free)	3000 / Tape & Reel
NCP432BVSNT1G / SC432BVSNT1G*	VRP	0.5%		SOT-23-3 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*SC Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS





TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE A

DATE 08 MAY 2012

	EMITTER BASE COLLECTOR								
	GATE SOURCE & SUBSTRATE DRAIN								
STYLE 11: PIN 1. 2. 3.	ANODE CATHODE & ANODE CATHODE	STYLE 12: PIN 1. 2. 3.	MAIN TERMINAL 1 Gate Main Terminal 2	STYLE 13: PIN 1. 2. 3.	ANODE 1 GATE CATHODE 2	STYLE 14: PIN 1. 2. 3.	EMITTER COLLECTOR BASE	STYLE 15: PIN 1. 2. 3.	ANODE 1 CATHODE ANODE 2
STYLE 16: PIN 1. 2. 3.	ANODE GATE CATHODE	STYLE 17: PIN 1. 2. 3.	COLLECTOR BASE EMITTER	STYLE 18: PIN 1. 2. 3.	ANODE CATHODE NOT CONNECTED	STYLE 19: PIN 1. 2. 3.	GATE ANODE CATHODE	STYLE 20: PIN 1. 2. 3.	NOT CONNECTED CATHODE ANODE
STYLE 21: PIN 1. 2. 3.	COLLECTOR EMITTER BASE	STYLE 22: PIN 1. 2. 3.	SOURCE GATE DRAIN	STYLE 23: PIN 1. 2. 3.	GATE SOURCE DRAIN	STYLE 24: PIN 1. 2. 3.	EMITTER Collector/Anode Cathode	STYLE 25: PIN 1. 2. 3.	MT 1 GATE MT 2
STYLE 26: PIN 1. 2. 3.	V _{CC} GROUND 2 OUTPUT	STYLE 27: PIN 1. 2. 3.	MT SUBSTRATE MT	STYLE 28: PIN 1. 2. 3.	CATHODE ANODE GATE	STYLE 29: PIN 1. 2. 3.	NOT CONNECTED ANODE CATHODE	STYLE 30: PIN 1. 2. 3.	DRAIN GATE SOURCE
STYLE 31: PIN 1. 2. 3.	GATE DRAIN SOURCE	STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN INPUT OUTPUT	STYLE 34: PIN 1. 2. 3.	INPUT Ground Logic	STYLE 35: PIN 1. 2. 3.	GATE COLLECTOR EMITTER

DOCUMENT NUMBER:	98AON52857E	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.					
DESCRIPTION:	TO-92 (TO-226) 1 WATT		PAGE 2 OF 2				

ON Semiconductor and us are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.





© Semiconductor Components Industries, LLC, 2019





*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.							
DESCRIPTION: SOIC-8 NB									
ON Semiconductor reserves the right the suitability of its products for any pa	ON Semiconductor and ware trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.								

SOIC-8 NB CASE 751-07 ISSUE AK

STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER EMITTER 5. BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: CATHODE 1 PIN 1. 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT 3. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: PIN 1. GROUND BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE P-SOURCE 3 P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE 2. ANODE SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC COMMON CATHODE/VCC 3 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 COMMON ANODE/GND 8. STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. 4. DRAIN, #2 GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 DRAIN 1 7. 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. LINE 1 OUT 8. STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. SOURCE SOURCE 6. SOURCE 7. 8 DRAIN

DATE 16 FEB 2011

STYLE 4: ANODE ANODE PIN 1. 2. ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 3. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. 4. GATE 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.					
DESCRIPTION: SOIC-8 NB PAGE 2 OF 2							
ON Semiconductor and ()) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the							

SOURCE 1/DRAIN 2

7.

8. GATE 1

7.

8

rights of others

COLLECTOR, #1

COLLECTOR, #1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor date sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use a a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor houteds for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

TECHNICAL SUPPORT

ON Semiconductor Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800–282–9855 Toll Free USA/Canada Phone: 011 421 33 790 2910 Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative